

## IGBT

High speed IGBT in Trench and Fieldstop technology  
recommended in combination with SiC Diode IDH15S120

## IGW40N120H3

1200V high speed switching series third generation

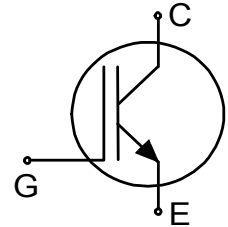
Data sheet

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**Features:**

TRENCHSTOP™ technology offering

- best in class switching performance: less than 500µJ total switching losses achievable
- very low  $V_{CEsat}$
- low EMI
- maximum junction temperature 175°C
- qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>



**Applications:**

- solar inverters
- uninterruptible power supplies
- welding converters
- converters with high switching frequency



**Package pin definition:**

- Pin 1 - gate
- Pin 2 & backside - collector
- Pin 3 - emitter



**Key Performance and Package Parameters**

Type	$V_{CE}$	$I_C$	$V_{CEsat}, T_{vj}=25^{\circ}C$	$T_{vjmax}$	Marking	Package
IGW40N120H3	1200V	40A	2.05V	175°C	G40H1203	PG-TO247-3